

IN THE CLAIMS

Please amend the claims as follows:

Claims 1-37 (Canceled).

Claim 38 (New): A ceramic substrate for a semiconductor producing/examining device having a conductor formed inside of the ceramic substrate,

wherein said ceramic substrate has an impurity element-existent area where an impurity element is locally distributed in triple points of crystal grains, and an impurity element-nonexistent area where an impurity element is not locally distributed in the triple points of crystal grains.

Claim 39 (New): The ceramic substrate according to claim 38, wherein said impurity element is at least one selected from the group consisting of boron, sodium, calcium, silicon and a sintering aid.

Claim 40 (New): The ceramic substrate according to claim 38, wherein said impurity element is at least one selected from the group consisting of Si, Y, and O.

Claim 41 (New): The ceramic substrate according to claim 38, wherein said ceramic substrate comprises a nitride ceramic, a carbide ceramic or an oxide ceramic.

Claim 42 (New): The ceramic substrate according to claim 38, wherein said ceramic substrate comprises aluminum nitride or silicon carbide.

Claim 43 (New): The ceramic substrate according to claim 38, wherein
said ceramic substrate is capable of use at a temperature of 150°C to 200°C.

Claim 44 (New): A semiconductor producing/examining device comprising the
ceramic substrate claimed in claim 38.

Claim 45 (New): The ceramic substrate according to claim 38, wherein
the thermal conductivity of said ceramic substrate is 100 W/m·K or more.

Claim 46 (New) The ceramic substrate according to claim 38, wherein
said ceramic substrate has a diameter of 200 mm or more.

Claim 47 (New): The ceramic substrate according to claim 38, wherein
said ceramic substrate has a diameter of 300 mm or more.

Claim 48 (New): The ceramic substrate according to claim 38, wherein
said ceramic substrate has a thickness of 25 mm or less.

Claim 49 (New): The ceramic substrate according to claim 38, wherein
a percentage of said impurity element-existent area becomes larger towards the center
of said ceramic substrate.

Claim 50 (New): A ceramic substrate for a semiconductor producing/examining
device having a conductor formed on a surface of the ceramic substrate,

wherein said ceramic substrate has an impurity element-existent area where an impurity element is locally distributed in triple points of crystal grains, and an impurity element-nonexistent area where an impurity element is not locally distributed in the triple points of crystal grains.

Claim 51 (New): The ceramic substrate according to claim 50, wherein said impurity element is at least one selected from the group consisting of boron, sodium, calcium, silicon and a sintering aid.

Claim 52 (New): The ceramic substrate according to claim 50, wherein said impurity element is at least one selected from the group consisting of Si, Y, and O.

Claim 53 (New): The ceramic substrate according to claim 50, wherein said ceramic substrate comprises a nitride ceramic, a carbide ceramic or an oxide ceramic.

Claim 54 (New): The ceramic substrate according to claim 50, wherein said ceramic substrate comprises aluminum nitride or silicon carbide.

Claim 55 (New): The ceramic substrate according to claim 50, wherein said ceramic substrate is capable of use at a temperature of 150°C to 200°C.

Claim 56 (New): A semiconductor producing/examining device comprising the ceramic substrate claimed in claim 50.

Claim 57 (New): The ceramic substrate according to claim 50, wherein the thermal conductivity of said ceramic substrate is 100 W/m • K or more.

Claim 58 (New): The ceramic substrate according to claim 50, wherein said ceramic substrate has a diameter of 200 mm or more.

Claim 59 (New): The ceramic substrate according to claim 50, wherein said ceramic substrate has a diameter of 300 mm or more.

Claim 60 (New): The ceramic substrate according to claim 50, wherein said ceramic substrate has a thickness of 25 mm or less.

Claim 61 (New): The ceramic substrate according to claim 50, wherein a percentage of said impurity element-existent area becomes larger towards the center of said ceramic substrate.

Claim 62 (New): A ceramic substrate comprising impurity element-existent area where an impurity element is locally distributed in triple points of crystal grains, and an impurity element-nonexistent area where an impurity element is not locally distributed in the triple points of crystal grains.

Claim 63 (New): The ceramic substrate according to claim 62, wherein said impurity element is at least one selected from the group consisting of boron, sodium, calcium, silicon and a sintering aid.

Claim 64 (New): The ceramic substrate according to claim 62, wherein
said impurity element is at least one selected from the group consisting of Si, Y, and
O.

Claim 65 (New): The ceramic substrate according to claim 62, wherein
said ceramic substrate comprises a nitride ceramic, a carbide ceramic or an oxide
ceramic.

Claim 66 (New): The ceramic substrate according to claim 62, wherein
said ceramic substrate comprises aluminum nitride or silicon carbide.

Claim 67 (New): The ceramic substrate according to claim 62, wherein
said ceramic substrate is capable of use at a temperature of 150°C to 200°C.

BASIS FOR THE AMENDMENT

Claims 38-67 are active in the present application. Claims 1-37 are canceled claims. Support for Claims 38, 50 and 62 is found on page 6, lines 21-31. Support for new Claims 39, 51 and 63 is found on page 6, lines 2-8. Support for new Claims 40, 52 and 64 is found in Figure 16. Support for new Claims 41, 53 and 65 is found on page 12, lines 11-13. Support for new Claims 42, 54 and 66 is found on page 12, lines 14-19. Support for new Claims 43, 55 and 67 is found on page 10, lines 23-26. Support for new Claims 44 and 56 is found on page 1, lines 6-14. Support for new Claims 45 and 57 is found on page 16, lines 26-27. Support for new Claims 46 and 58 is found on page 11, lines 31-32. Support for new Claims 47 and 59 is found on page 11, lines 32-33. Support for new Claims 48 and 60 is found on page 12, lines 1-2. Support for new Claims 49 and 61 is found on page 7, lines 11-13.

No new matter is added.